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## 1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a SOT78 (TO-220AB) plastic package intended for use in applications requiring very high inrush current capability, high thermal cycling performance and high junction temperature capability $\left(\mathrm{T}_{\mathrm{j}(\max )}=150^{\circ} \mathrm{C}\right)$.

## 2. Features and benefits

- High junction operating temperature capability
- High thermal cycling performance
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Very high current surge capability


## 3. Applications

- Ignition circuits
- Motor control
- Protection circuits e.g. SMPS inrush current
- Voltage regulation


## 4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {RRM }}$ | repetitive peak reverse voltage |  | - | - | 800 | V |
| $\left.\mathrm{I}_{\text {( }} \mathrm{AV}\right)$ | average on-state current | half sine wave; $\mathrm{T}_{\mathrm{mb}} \leq 134^{\circ} \mathrm{C}$; Fig. 1 | - | - | 10.2 | A |
| $\mathrm{I}_{\text {( } \mathrm{RMS} \text { ) }}$ | RMS on-state current | half sine wave; $\mathrm{T}_{\mathrm{mb}} \leq 134^{\circ} \mathrm{C}$; Fig. 2; Fig. 3 | - | - | 16 | A |
| $\mathrm{I}_{\text {TSM }}$ | non-repetitive peak onstate current | half sine wave; $\mathrm{T}_{\mathrm{j} \text { (init) }}=25^{\circ} \mathrm{C}$; $\mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}$; Fig. 4; Fig. 5 | - | - | 210 | A |
|  |  | half sine wave; $\mathrm{T}_{\mathrm{j}(\text { (init })}=25^{\circ} \mathrm{C}$; $\mathrm{t}_{\mathrm{p}}=8.3 \mathrm{~ms}$ | - | - | 231 | A |
| $\mathrm{T}_{\mathrm{j}}$ | junction temperature |  | - | - | 150 | ${ }^{\circ} \mathrm{C}$ |
| Static characteristics |  |  |  |  |  |  |
| $\mathrm{I}_{\text {GT }}$ | gate trigger current | $\mathrm{V}_{\mathrm{D}}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{T}}=0.1 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; Fig. 7 | - | 4.5 | 25 | mA |
| Dynamic characteristics |  |  |  |  |  |  |


| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{dV}_{\mathrm{D}} / \mathrm{dt}$ | rate of rise of off-state <br> voltage | $\mathrm{V}_{\mathrm{DM}}=536 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C} ;\left(\mathrm{V}_{\mathrm{DM}}=67 \%\right.$ <br> of $\left.\mathrm{V}_{\mathrm{DRM}}\right) ;$ exponential waveform; gate <br> open circuit | 300 | - | - | $\mathrm{V} / \mathrm{\mu s}$ |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
| :---: | :---: | :---: | :---: | :---: |
| 1 | K | cathode |  | $\begin{gathered} \text { A } \\ \text { sym037 } \\ \substack{\text { G }} \\ \hline \end{gathered}$ |
| 2 | A | anode |  |  |
| 3 | G | gate |  |  |
| mb | A | mounting base; connected to anode |  |  |

## 6. Ordering information

Table 3. Ordering information

| Type number | Package |  |  |
| :--- | :--- | :--- | :--- |
|  | Name | Description | Version |
| TYN16-800RT | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting <br> hole; 3-lead TO-220AB | SOT78 |

## 7. Limiting values

Table 4. Limiting values
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {DRM }}$ | repetitive peak off-state voltage |  | - | 800 | V |
| $\mathrm{V}_{\text {RRM }}$ | repetitive peak reverse voltage |  | - | 800 | V |
| $\mathrm{I}_{\text {(AV) }}$ | average on-state current | half sine wave; $\mathrm{T}_{\mathrm{mb}} \leq 134^{\circ} \mathrm{C}$; Fig. 1 | - | 10.2 | A |
| $\mathrm{I}_{\text {(RMS) }}$ | RMS on-state current | half sine wave; $\mathrm{T}_{\mathrm{mb}} \leq 134^{\circ} \mathrm{C}$; Fig. 2; Fig. 3 | - | 16 | A |
| $\mathrm{I}_{\text {TSM }}$ | non-repetitive peak onstate current | half sine wave; $\mathrm{T}_{\mathrm{j}(\text { (init })}=25^{\circ} \mathrm{C}$; $\mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}$; Fig. 4; Fig. 5 | - | 210 | A |
|  |  | half sine wave; $\mathrm{T}_{\mathrm{j} \text { (init) }}=25^{\circ} \mathrm{C} ; \mathrm{t}_{\mathrm{p}}=8.3 \mathrm{~ms}$ | - | 231 | A |
| $\mathrm{I}^{2} \mathrm{t}$ | $1^{2} t$ for fusing | $\mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms} ; \mathrm{SIN}$ | - | 220.5 | $A^{2} \mathrm{~S}$ |
| $\mathrm{dl}_{T} / \mathrm{dt}$ | rate of rise of on-state current | $\mathrm{I}_{\mathrm{G}}=50 \mathrm{~mA}$ | - | 50 | A/ $\mu \mathrm{s}$ |
| $\mathrm{I}_{\mathrm{GM}}$ | peak gate current |  | - | 5 | A |
| $\mathrm{V}_{\text {RGM }}$ | peak reverse gate voltage |  | - | 5 | V |
| $\mathrm{P}_{\mathrm{GM}}$ | peak gate power |  | - | 20 | W |
| $\mathrm{P}_{\mathrm{G}(\mathrm{AV})}$ | average gate power | over any 20 ms period | - | 1 | W |
| $\mathrm{T}_{\text {stg }}$ | storage temperature |  | -40 | 150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | junction temperature |  | - | 150 | ${ }^{\circ} \mathrm{C}$ |



Fig. 1. Total power dissipation as a function of average on-state current; maximum values


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values


Fig. 3. RMS on-state current as a function of surge duration; maximum values


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values


Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

## 8. Thermal characteristics

Table 5. Thermal characteristics

| Symbol | Parameter | Conditions |  | Min | Typ | Max | Unit |
| :--- | :--- | :--- | :--- | :--- | :--- | :--- | :--- |
| $\mathrm{R}_{\text {th(j-mb) }}$ | thermal resistance <br> from junction to <br> mounting base | Fig. 6 |  | - | - | 1.1 | K/W |
| $\mathrm{R}_{\text {th(j-a) }}$ | thermal resistance <br> from junction to <br> ambient free air | in free air |  | - | 60 | - | K/W |



Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 9. Characteristics

Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Static characteristics |  |  |  |  |  |  |
| $\mathrm{I}_{\mathrm{GT}}$ | gate trigger current | $\mathrm{V}_{\mathrm{D}}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{T}}=0.1 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; Fig. 7 | - | 4.5 | 25 | mA |
| $\mathrm{I}_{\mathrm{L}}$ | latching current | $V_{D}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{G}}=0.1 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; Fig. 8 | - | 21 | 60 | mA |
| $\mathrm{I}_{\mathrm{H}}$ | holding current | $V_{D}=12 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; Fig. 9 | - | 16 | 40 | mA |
| $V_{T}$ | on-state voltage | $\mathrm{I}_{\mathrm{T}}=32 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} ;$ Fig. 10 | - | 1.2 | 1.5 | V |
| $V_{G T}$ | gate trigger voltage | $\begin{aligned} & V_{D}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{T}}=0.1 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} ; \\ & \text { Fig. } 11 \end{aligned}$ | - | 0.7 | 1.3 | V |
|  |  | $\begin{aligned} & V_{D}=400 \mathrm{~V} ; I_{T}=0.1 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C} \text {; } \\ & \text { Fig. } 11 \end{aligned}$ | 0.2 | 0.4 | - | V |
| $\mathrm{I}_{\mathrm{D}}$ | off-state current | $\mathrm{V}_{\mathrm{D}}=800 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$ | - | 0.2 | 1 | mA |
| $\mathrm{I}_{\mathrm{R}}$ | reverse current | $\mathrm{V}_{\mathrm{R}}=800 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$ | - | 0.2 | 1 | mA |
| Dynamic characteristics |  |  |  |  |  |  |
| $\mathrm{dV} \mathrm{V}_{\mathrm{D}} / \mathrm{dt}$ | rate of rise of off-state voltage | $V_{D M}=536 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C} ;\left(\mathrm{V}_{\mathrm{DM}}=67 \%\right.$ of $\mathrm{V}_{\mathrm{DRM}}$ ); exponential waveform; gate open circuit | 300 | - | - | $\mathrm{V} / \mathrm{\mu s}$ |



Fig. 7. Normalized gate trigger current as a function of junction temperature


Fig. 8. Normalized latching current as a function of junction temperature


Fig. 9. Normalized holding current as a function of junction temperature

$\mathrm{V}_{\mathrm{o}}=1.0336 \mathrm{~V} ; \mathrm{R}_{\mathrm{s}}=0.0141 \Omega$
(1) $\mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$; typical values
(2) $\mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$; maximum values
(3) $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

## 10. Package outline



DIMENSIONS (mm are the original dimensions)

| UNIT | $\mathbf{A}$ | $\mathbf{A}_{\mathbf{1}}$ | $\mathbf{b}$ | $\mathbf{b}_{\mathbf{1}} \mathbf{1 2 )}^{\mathbf{2})}$ | $\mathbf{b}_{\mathbf{2}}{ }^{(2)}$ | $\mathbf{c}$ | $\mathbf{D}$ | $\mathbf{D}_{\mathbf{1}}$ | $\mathbf{E}$ | $\mathbf{e}$ | $\mathbf{L}$ | $\mathbf{L}_{\mathbf{1}} \mathbf{1}^{\mathbf{1}}$ | $\mathbf{L}_{\mathbf{2}}{ }^{(\mathbf{1})}$ <br> $\mathbf{m a x}$. | $\mathbf{p}$ | $\mathbf{q}$ | $\mathbf{Q}$ |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| mm | 4.7 | 1.40 | 0.9 | 1.6 | 1.3 | 0.7 | 16.0 | 6.6 | 10.3 | 2.54 | 15.0 | 3.30 | 3.0 | 3.8 | 3.0 | 2.6 |
|  | 4.1 | 1.25 | 0.6 | 1.0 | 1.0 | 0.4 | 15.2 | 5.9 | 9.7 | 2.54 | 12.8 | 2.79 | 3.0 | 3.5 | 2.7 | 2.2 |

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

| OUTLINE <br> VERSION | REFERENCES |  |  |  | EUROPEAN <br> PROJECTION | ISSUE DATE |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | IEC | JEDEC | JEITA |  |  |  |

Fig. 12. Package outline TO-220AB (SOT78)

## 11. Legal information

## Data sheet status

| Document <br> status [1][2] | Product <br> status [3] | Definition |
| :--- | :--- | :--- |
| Objective <br> [short] data <br> sheet | Development | This document contains data from <br> the objective specification for product <br> development. |
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| Product <br> [short] data <br> sheet | Production | This document contains the product <br> specification. |

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